

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

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ABSTRACT OF THE DISCLOSURE

The resist film is provided on the surface of the substrate having electrodes, and openings are provided in the resist film at positions of the electrodes on the substrate. The first metal is supplied into the openings. The first metal is then heated to melt and coagulate it. The second metal is then supplied into the openings on the first metal. The first metal and the second metal are heated to melt and coagulate them. The resist film is finally removed. By this method, excellent solder bumps can be formed on the substrate without remnants of the resist film being left on the substrate.